



**THE DATASHEET OF  
SPZT3904T1G**



# PZT3904T1G

## General Purpose Transistor

### NPN Silicon

#### Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	40	Vdc
Collector-Base Voltage	$V_{CBO}$	60	Vdc
Emitter-Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current - Continuous	$I_C$	200	mAdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### THERMAL CHARACTERISTICS

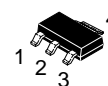
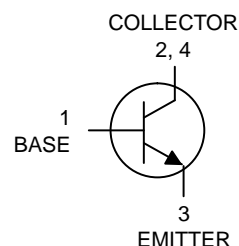
Characteristic	Symbol	Max	Unit
Total Device Dissipation (Note 1) $T_A = 25^\circ\text{C}$	$P_D$	1.5 12	W mW/°C
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	83.3	°C/W
Thermal Resistance Junction-to-Lead #4	$R_{\theta JA}$	35	°C/W
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	°C

1. FR-4 with 1 oz and 713 mm<sup>2</sup> of copper area.



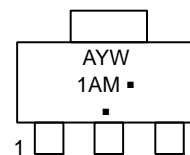
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**SOT-223  
CASE 318E  
STYLE 1**

#### MARKING DIAGRAM



1AM = Specific Device Code  
 A = Assembly Location  
 Y = Year  
 W = Work Week  
 ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

Device	Package	Shipping†
PZT3904T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel
SPZT3904T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b> (Note 2)				
Collector–Emitter Breakdown Voltage (Note 3) (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	40	–	V <sub>dc</sub>
Collector–Base Breakdown Voltage (I <sub>C</sub> = 10 μA <sub>dc</sub> , I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	60	–	
Emitter–Base Breakdown Voltage (I <sub>E</sub> = 10 μA <sub>dc</sub> , I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	6.0	–	
Base Cutoff Current (V <sub>CE</sub> = 30 V <sub>dc</sub> , V <sub>EB</sub> = 3.0 V <sub>dc</sub> )	I <sub>BL</sub>	–	50	nA <sub>dc</sub>
Collector Cutoff Current (V <sub>CE</sub> = 30 V <sub>dc</sub> , V <sub>EB</sub> = 3.0 V <sub>dc</sub> )	I <sub>CEX</sub>	–	50	

## ON CHARACTERISTICS

DC Current Gain (Note 2) (I <sub>C</sub> = 0.1 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> ) (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> ) (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> ) (I <sub>C</sub> = 50 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> ) (I <sub>C</sub> = 100 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> )	H <sub>FE</sub>	40 70 100 60 30	– – 300 – –	–
Collector–Emitter Saturation Voltage (Note 3) (I <sub>C</sub> = 10 mA <sub>dc</sub> , I <sub>B</sub> = 1.0 mA <sub>dc</sub> ) (I <sub>C</sub> = 50 mA <sub>dc</sub> , I <sub>B</sub> = 5.0 mA <sub>dc</sub> )	V <sub>CE(sat)</sub>	– –	0.2 0.3	V <sub>dc</sub>
Base–Emitter Saturation Voltage (Note 3) (I <sub>C</sub> = 10 mA <sub>dc</sub> , I <sub>B</sub> = 1.0 mA <sub>dc</sub> ) (I <sub>C</sub> = 50 mA <sub>dc</sub> , I <sub>B</sub> = 5.0 mA <sub>dc</sub> )	V <sub>BE(sat)</sub>	0.65 –	0.85 0.95	V <sub>dc</sub>

## SMALL–SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 20 V <sub>dc</sub> , f = 100 MHz)	f <sub>T</sub>	300	–	MHz
Output Capacitance (V <sub>CB</sub> = 5.0 V <sub>dc</sub> , I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	–	5.0	pF
Input Capacitance (V <sub>EB</sub> = 0.5 V <sub>dc</sub> , I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ibo</sub>	–	8.0	
Input Impedance (V <sub>CE</sub> = 10 V <sub>dc</sub> , I <sub>C</sub> = 1.0 mA <sub>dc</sub> , f = 1.0 kHz)	h <sub>ie</sub>	1.0	10	kΩ
Voltage Feedback Ratio (V <sub>CE</sub> = 10 V <sub>dc</sub> , I <sub>C</sub> = 1.0 mA <sub>dc</sub> , f = 1.0 kHz)	h <sub>re</sub>	0.5	8.0	X 10 <sup>–4</sup>
Small–Signal Current Gain (V <sub>CE</sub> = 10 V <sub>dc</sub> , I <sub>C</sub> = 1.0 mA <sub>dc</sub> , f = 1.0 kHz)	h <sub>fe</sub>	100	400	–
Output Admittance (V <sub>CE</sub> = 10 V <sub>dc</sub> , I <sub>C</sub> = 1.0 mA <sub>dc</sub> , f = 1.0 kHz)	h <sub>oe</sub>	1.0	40	μMhos
Noise Figure (V <sub>CE</sub> = 5.0 V <sub>dc</sub> , I <sub>C</sub> = 100 μA <sub>dc</sub> , R <sub>S</sub> = 1.0 kΩ, f = 1.0 kHz)	nF	–	5.0	dB

## SWITCHING CHARACTERISTICS

Delay Time	(V <sub>CC</sub> = 3.0 V <sub>dc</sub> , V <sub>BE</sub> = –0.5 V <sub>dc</sub> , I <sub>C</sub> = 10 mA <sub>dc</sub> , I <sub>B1</sub> = 1.0 mA <sub>dc</sub> )	t <sub>d</sub>	–	35	ns
Rise Time		t <sub>r</sub>	–	35	
Storage Time	(V <sub>CC</sub> = 3.0 V <sub>dc</sub> , I <sub>C</sub> = 10 mA <sub>dc</sub> , I <sub>B1</sub> = I <sub>B2</sub> = 1.0 mA <sub>dc</sub> )	t <sub>s</sub>	–	200	
Fall Time		t <sub>f</sub>	–	50	

2. FR–5 = 1.0 × 0.75 × 0.062 in.

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

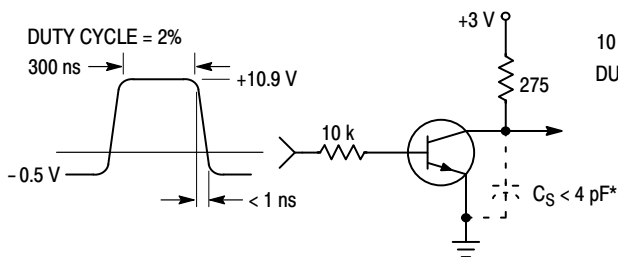


Figure 1. Delay and Rise Time Equivalent Test Circuit

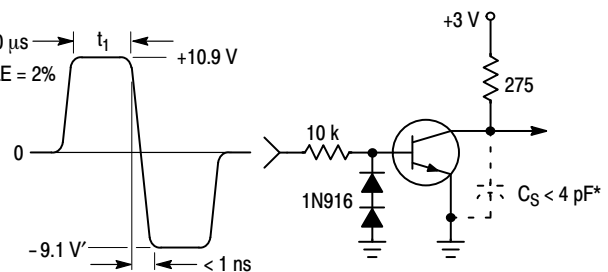


Figure 2. Storage and Fall Time Equivalent Test Circuit

\* Total shunt capacitance of test jig and connectors

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## TYPICAL TRANSIENT CHARACTERISTICS

—  $T_J = 25^\circ\text{C}$   
 - - -  $T_J = 125^\circ\text{C}$

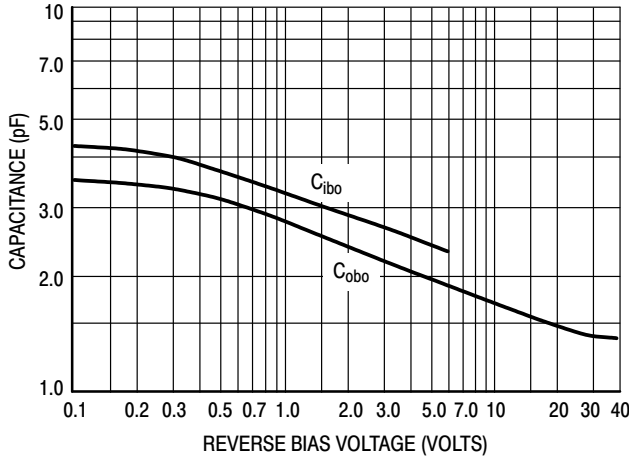


Figure 3. Capacitance

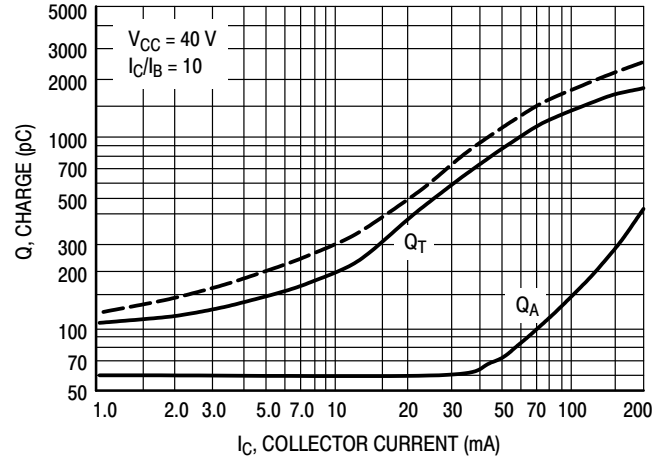


Figure 4. Charge Data

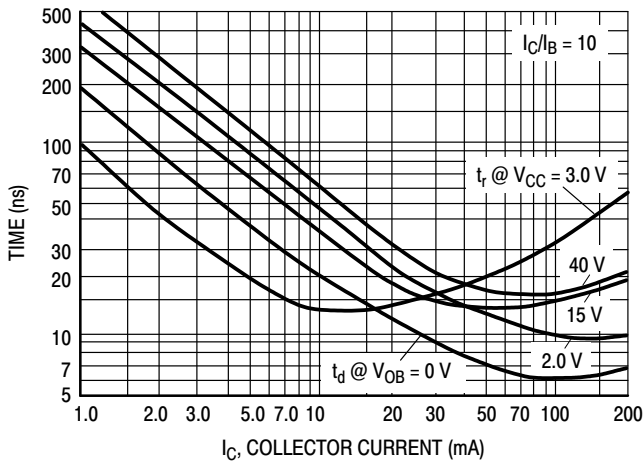


Figure 5. Turn-On Time

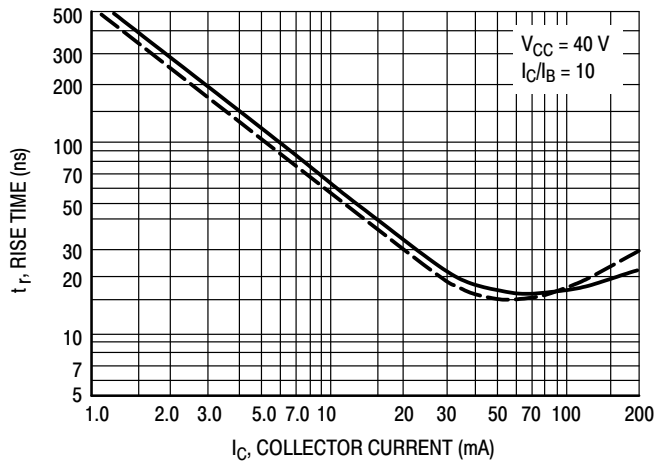


Figure 6. Rise Time

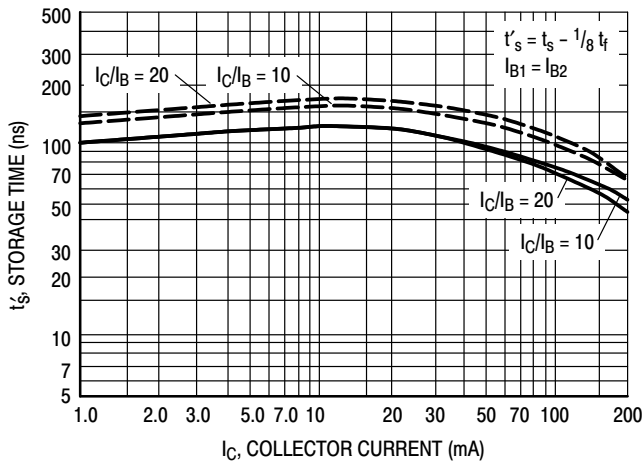


Figure 7. Storage Time

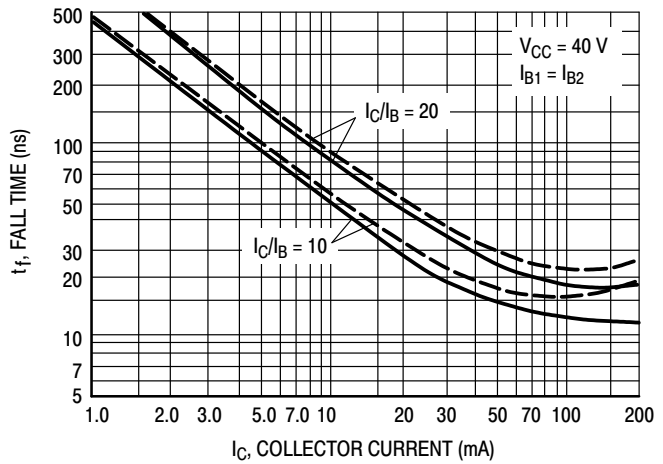


Figure 8. Fall Time

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## TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

( $V_{CE} = 5.0$  Vdc,  $T_A = 25^\circ\text{C}$ , Bandwidth = 1.0 Hz)

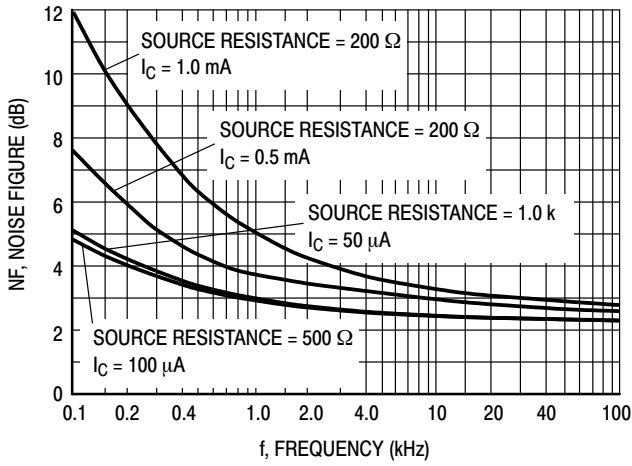


Figure 9.

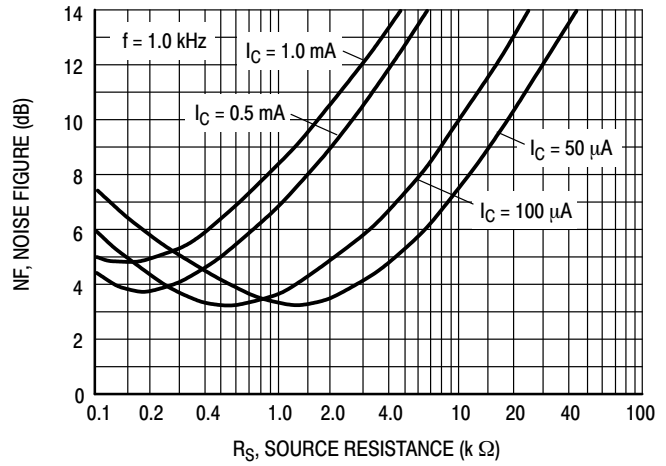


Figure 10.

## h PARAMETERS

( $V_{CE} = 10$  Vdc,  $f = 1.0$  kHz,  $T_A = 25^\circ\text{C}$ )

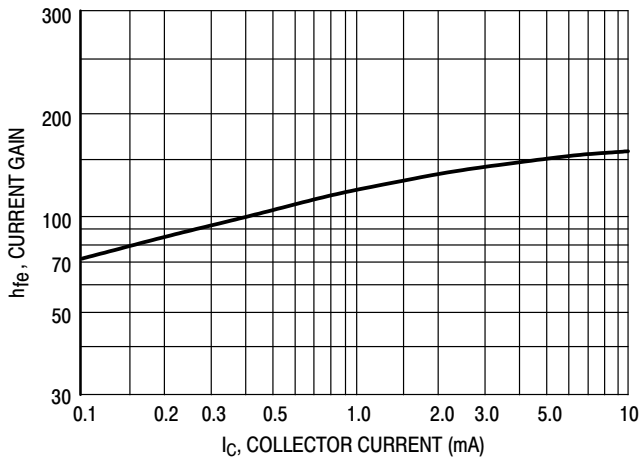


Figure 11. Current Gain

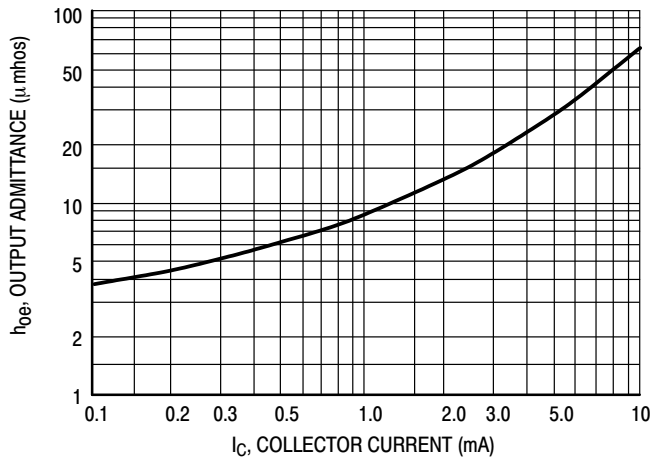


Figure 12. Output Admittance

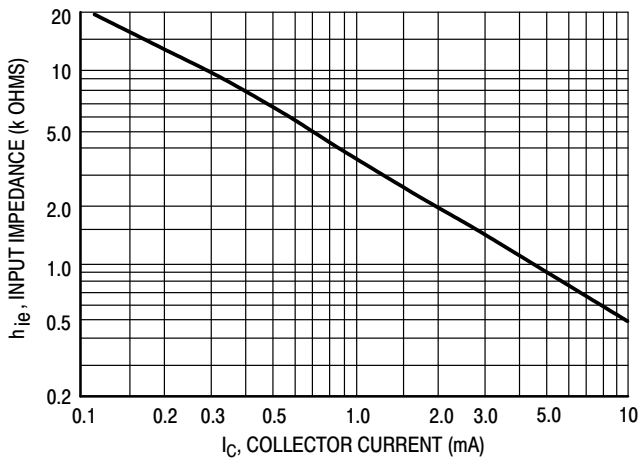


Figure 13. Input Impedance

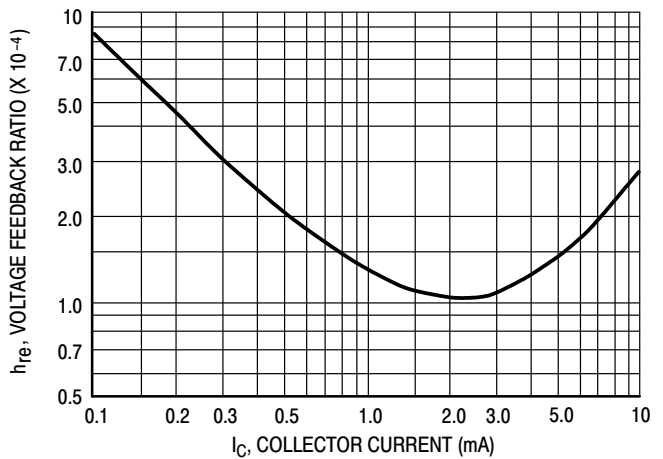


Figure 14. Voltage Feedback Ratio

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## TYPICAL STATIC CHARACTERISTICS

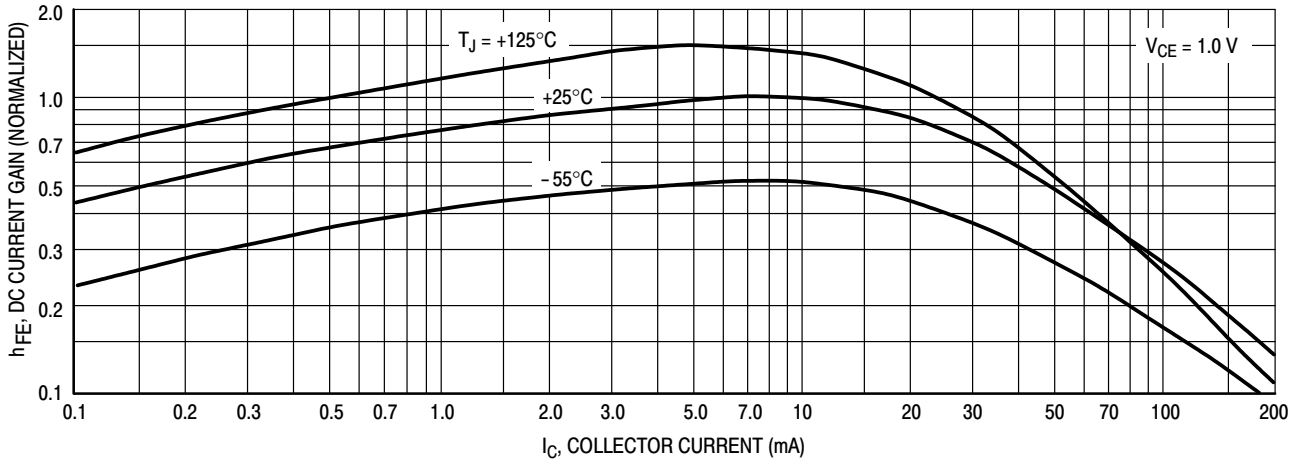


Figure 15. DC Current Gain

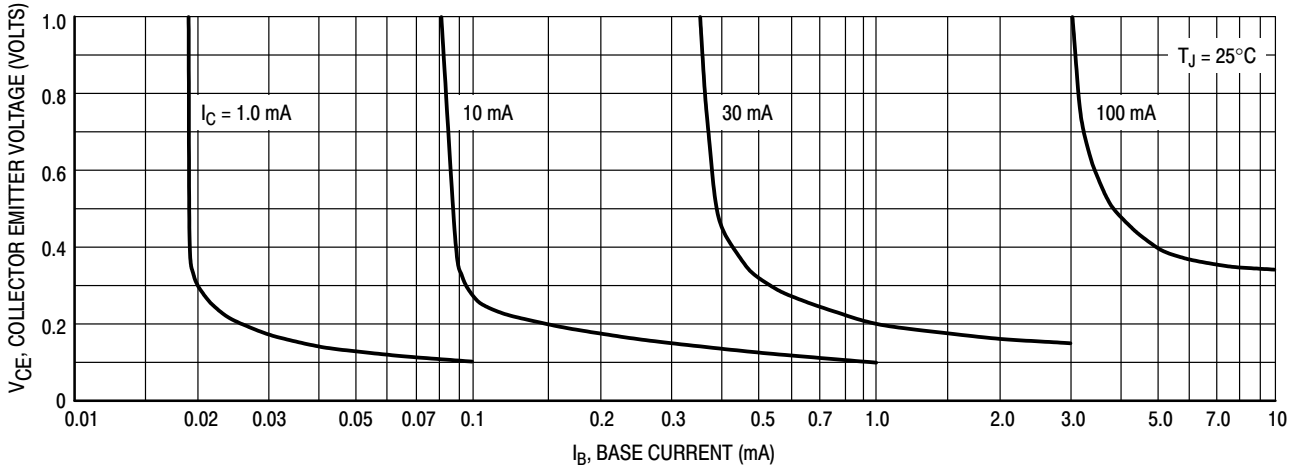


Figure 16. Collector Saturation Region

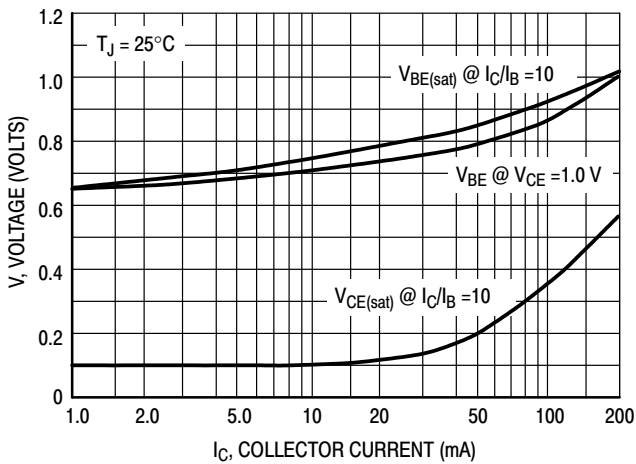


Figure 17. "ON" Voltages

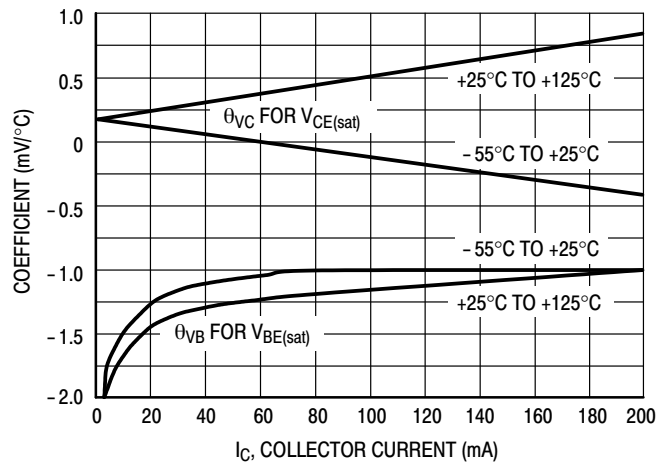
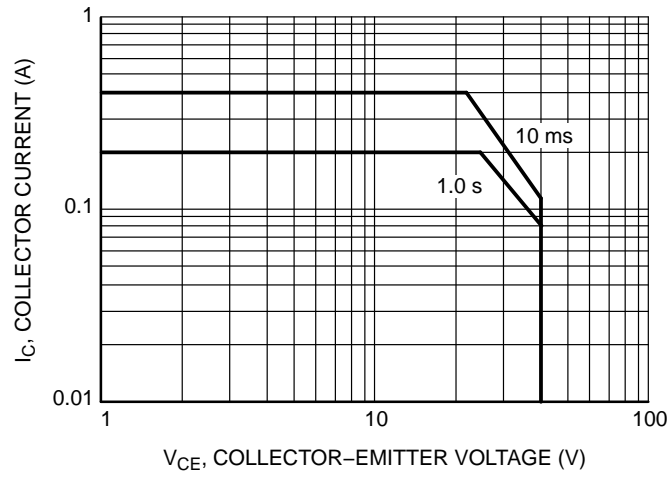


Figure 18. Temperature Coefficients

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## TYPICAL CHARACTERISTICS



**Figure 19. Safe Operating Area**

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

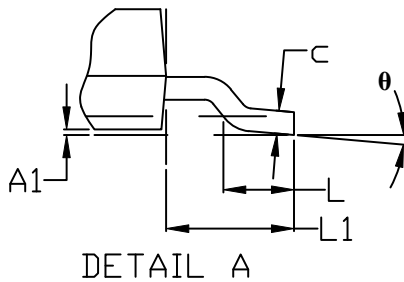
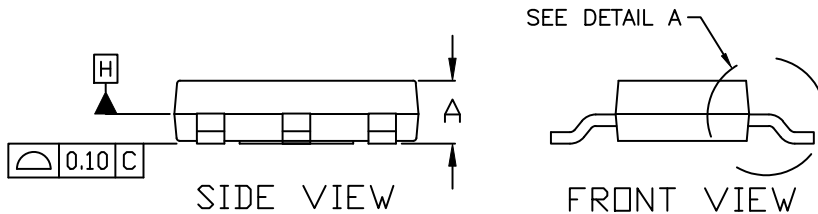
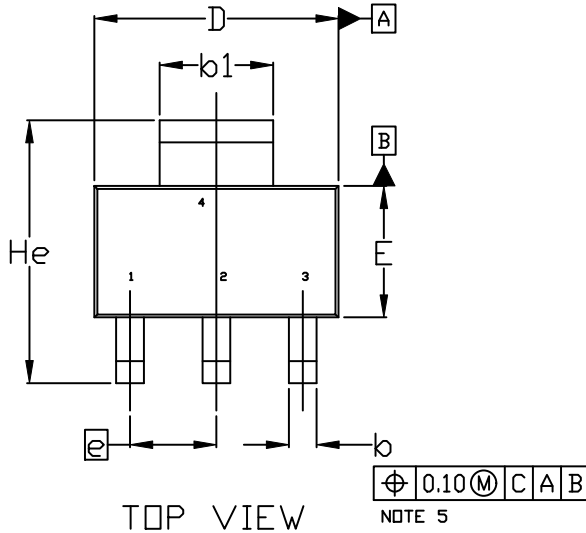
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SCALE 1:1

SOT-223 (TO-261)  
CASE 318E-04  
ISSUE R

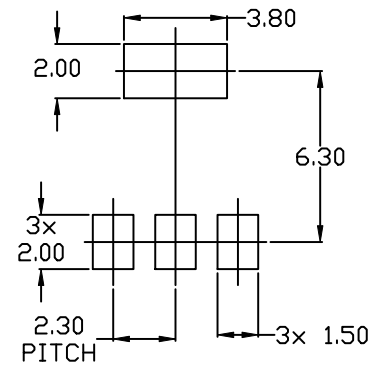
DATE 02 OCT 2018



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
4. DATUMS A AND B ARE DETERMINED AT DATUM H.
5. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.

MILLIMETERS			
DIM	MIN.	NOM.	MAX.
A	1.50	1.63	1.75
A1	0.02	0.06	0.10
b	0.60	0.75	0.89
b1	2.90	3.06	3.20
c	0.24	0.29	0.35
D	6.30	6.50	6.70
E	3.30	3.50	3.70
e	2.30 BSC		
L	0.20	---	---
L1	1.50	1.75	2.00
He	6.70	7.00	7.30
θ	0°	---	10°



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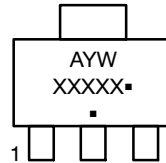
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**SOT-223 (TO-261)**  
**CASE 318E-04**  
**ISSUE R**

DATE 02 OCT 2018

- |                                                                              |                                                                             |                                                                               |                                                                       |                                                                       |
|------------------------------------------------------------------------------|-----------------------------------------------------------------------------|-------------------------------------------------------------------------------|-----------------------------------------------------------------------|-----------------------------------------------------------------------|
| <b>STYLE 1:</b><br>PIN 1. BASE<br>2. COLLECTOR<br>3. EMITTER<br>4. COLLECTOR | <b>STYLE 2:</b><br>PIN 1. ANODE<br>2. CATHODE<br>3. NC<br>4. CATHODE        | <b>STYLE 3:</b><br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE<br>4. DRAIN           | <b>STYLE 4:</b><br>PIN 1. SOURCE<br>2. DRAIN<br>3. GATE<br>4. DRAIN   | <b>STYLE 5:</b><br>PIN 1. DRAIN<br>2. GATE<br>3. SOURCE<br>4. GATE    |
| <b>STYLE 6:</b><br>PIN 1. RETURN<br>2. INPUT<br>3. OUTPUT<br>4. INPUT        | <b>STYLE 7:</b><br>PIN 1. ANODE 1<br>2. CATHODE<br>3. ANODE 2<br>4. CATHODE | <b>STYLE 8:</b><br>CANCELLED                                                  | <b>STYLE 9:</b><br>PIN 1. INPUT<br>2. GROUND<br>3. LOGIC<br>4. GROUND | <b>STYLE 10:</b><br>PIN 1. CATHODE<br>2. ANODE<br>3. GATE<br>4. ANODE |
| <b>STYLE 11:</b><br>PIN 1. MT 1<br>2. MT 2<br>3. GATE<br>4. MT 2             | <b>STYLE 12:</b><br>PIN 1. INPUT<br>2. OUTPUT<br>3. NC<br>4. OUTPUT         | <b>STYLE 13:</b><br>PIN 1. GATE<br>2. COLLECTOR<br>3. EMITTER<br>4. COLLECTOR |                                                                       |                                                                       |

**GENERIC  
 MARKING DIAGRAM\***




- A = Assembly Location
- Y = Year
- W = Work Week
- XXXXX = Specific Device Code
- = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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